PRELIMINARY

CYU01M16SFCU
MoBL3™

16-Mbit (1M x 16) Pseudo Static RAM

Features

- **Wide voltage range: 1.7V–1.95V**
- **Access Time: 70 ns**
- **Ultra-low active power**
  - **Typical active current: 3 mA @ f = 1 MHz**
  - **Typical active current: 18mA @ f = f_{max}**
- **Ultra low standby power**
- **16-word Page Mode**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Offered in a 48-ball BGA Package**
- **Operating Temperature: –40°C to +85°C**

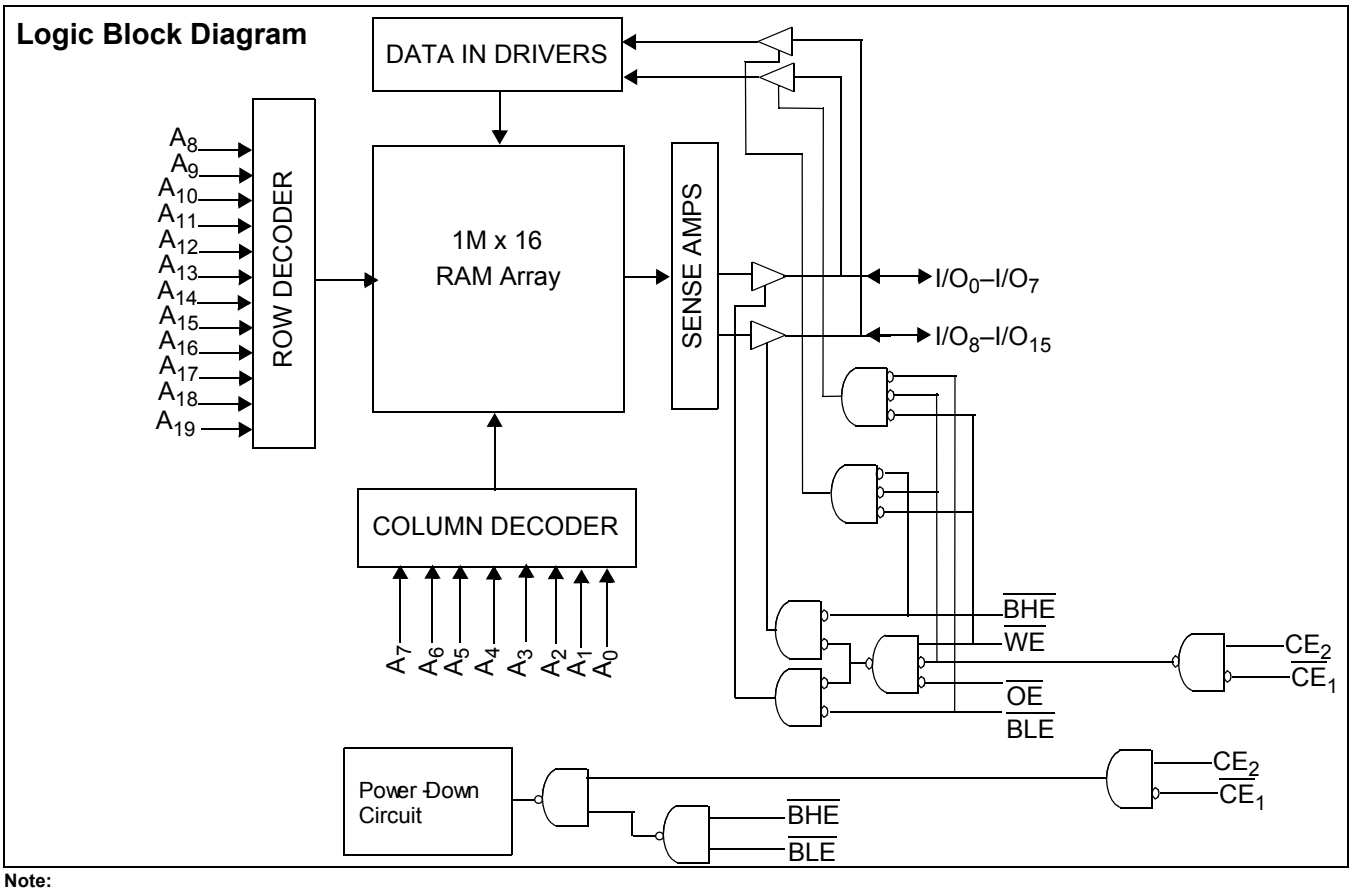
Functional Description[1]

The CYU01M16SFCU is a high-performance CMOS Pseudo Static RAM organized as 1M words by 16 bits that supports an asynchronous memory interface. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device can be put into standby mode when deselected ($\overline{CE}_1$ HIGH or CE_2 LOW or both $\overline{BHE}$ and $\overline{BLE}$ are HIGH). The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected ($\overline{CE}_1$ HIGH or CE_2 LOW), outputs are disabled ($\overline{OE}$ HIGH), both Byte High Enable and Byte Low Enable are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH), or during a write operation ($\overline{CE}_1$ LOW and CE_2 HIGH and $\overline{WE}$ LOW).

Writing to the device is accomplished by taking Chip Enable ($\overline{CE}_1$ LOW and CE_2 HIGH) and Write Enable ($\overline{WE}$) input LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{19}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{19}).

Reading from the device is accomplished by taking Chip Enables ($\overline{CE}_1$ LOW and CE_2 HIGH) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. Refer to the truth table for a complete description of read and write modes.

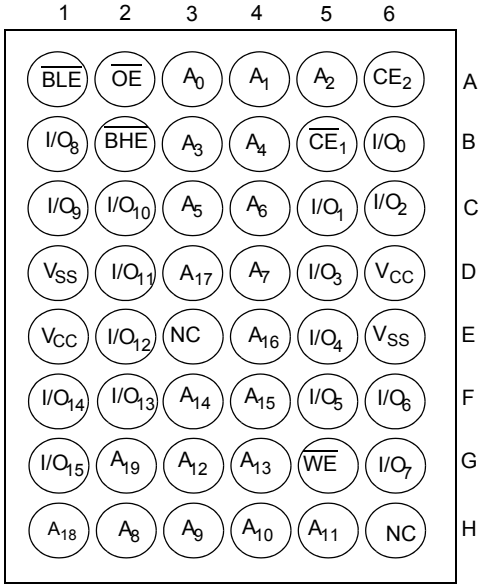
Logic Block Diagram



Note:
1. For best-practice recommendations, please refer to the Cypress application note “System Design Guidelines” on http://www.cypress.com.

Pin Configuration[2, 3]

48-Ball VFBGA
Top View

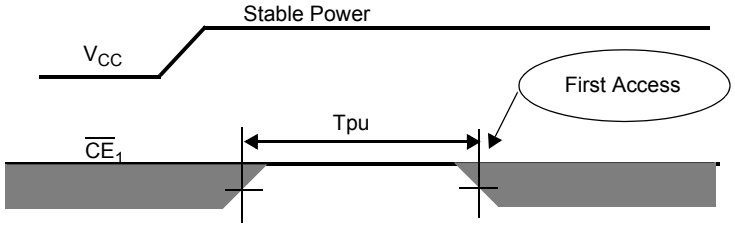


Product Portfolio[4]

Product	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I_{CC} (mA)				Standby I_{SB2} (μA)	
					f = 1MHz		f = f_{max}			
	Min.	Typ.[4]	Max.		Typ.[4]	Max.	Typ.[4]	Max.	Typ.[4]	Max.
CYU01M16SFCU	1.7	1.8	1.95	70	3	5	18	25	55	70

Power-up Characteristics

The initialization sequence is shown in the figure below. Chip Select should be $\overline{CE_1}$ HIGH or CE_2 LOW for at least 200 μs after V_{CC} has reached a stable value. No access must be attempted during this period of 200 μs.



Parameter	Description	Min.	Typ.	Max.	Unit
Tpu	Chip Enable Low After Stable V_{CC}	200			μs

Notes:
2. Ball H6 and E3 can be used to upgrade to a 32-Mbit and a 64-Mbit density, respectively.
3. NC "no connect" - not connected internally to the die.
4. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC}$ (typ) and $T_A = 25°C$. Tested initially and after design changes that may affect the parameters.

Page Mode

This device can be operated in a page read mode. This is accomplished by initiating a normal read of the device.

In order to operate the device in page mode, the upper order address bits should be fixed for four-word page access operation, all address bits except for A1 and A0 should be fixed until the page access is completed. For an eight-word page access, all address bits, except for A2, A1, and A0, should be fixed. For a sixteen-word page mode all address bits, except for A3, A2, A1, and A0, should be fixed.

The supported page lengths are four, eight, and sixteen words. Random page read is supported for all three four, eight, and sixteen-word page read options. Therefore, any address can be used as the starting address.

Please refer to the table below for an overview of the page read modes.

Page Mode Feature	4-Word Mode	8-Word Mode	16-Word Mode
Page Length	4 words	8 words	16 words
Page Read Corresponding Addresses	A1, A0	A2, A1, A0	A3, A2, A1, A0
Page Read Start Address	Don't Care	Don't Care	Don’t Care
Page Direction	Don't Care	Don't Care	Don’t Care

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....–65°C to +150°C

Ambient Temperature with Power Applied.....–55°C to +125°C

Supply Voltage to Ground Potential .–0.2V to V_{CCMAX} + 0.3V

DC Voltage Applied to Outputs in High Z State[5, 6, 7].....–0.2V to V_{CCMAX} + 0.3V

DC Input Voltage[5, 6, 7].....–0.2V to V_{CCMAX} + 0.3V

Output Current into Outputs (LOW).....20 mA

Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)

Latch-Up Current.....> 200 mA

Device	Range	Operating Temperature (T_A)	V_{CC}
CYU01M16SFCU	Industrial	–40°C to +85°C	1.7V to 1.95V

DC Electrical Characteristics (Over the Operating Range) [5, 6, 7]

Parameter	Description	Test Conditions	CYU01M16SFCU-70 ns			Unit
			Min.	Typ.[4]	Max.	
V_{CC}	Supply Voltage		1.7	1.8	1.95	V
V_{OH}	Output HIGH Voltage	I_{OH} = –0.1 mA V_{CC}= 1.7V to 1.95V	V_{CC} – 0.2			V
V_{OL}	Output LOW Voltage	I_{OL} = 0.1 mA V_{CC}= 1.7V to 1.95V			0.2	V
V_{IH}	Input HIGH Voltage	V_{CC}= 1.7V to 1.95V	0.8 * V_{CC}		V_{CC} + 0.3V	V
V_{IL}	Input LOW Voltage	V_{CC}= 1.7V to 1.95V	–0.2		0.2 * V_{CC}	V
I_{IX}	Input Leakage Current	GND ≤ V_{IN} ≤ V_{CC}	–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_{OUT} ≤ V_{CC}	–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = $1/t_{RC}$; V_{CC}= V_{CCmax}, I_{OUT} = 0 mA, CMOS levels		18	25	mA
		f = 1MHz		3	5	mA
I_{SB1}	Automatic CE Power-Down Current — CMOS Inputs	$\overline{CE_1}$ ≥ V_{CC} – 0.2V, CE_2 ≤ 0.2V, V_{IN} > V_{CC} – 0.2V, V_{IN} < 0.2V f = f_{MAX} (Address and Data Only), f = 0 (OE, WE, BHE and BLE), V_{CC} = 3.60V		55	70	µA
I_{SB2}	Automatic CE Power-Down Current — CMOS Inputs	$\overline{CE_1}$ ≥ V_{CC} – 0.2V, CE_2 ≤ 0.2V V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC}=V_{CCMAX}		55	70	µA

Capacitance[8]

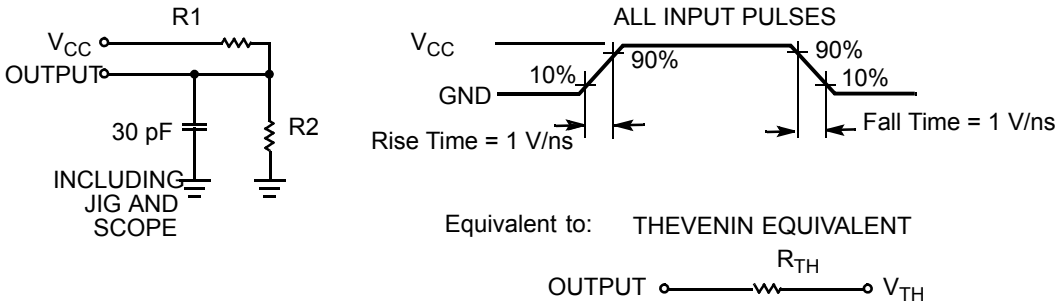
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	8	pF
C_{OUT}	Output Capacitance		8	pF

Thermal Resistance[8]

Parameter	Description	Test Conditions	VFBGA	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedence, per EIA / JESD51.	56	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		11	°C/W

Notes:
5. $V_{IL(MIN)}$ = –0.5V for pulse durations less than 20 ns.
6. $V_{IH(Max)}$ = V_{CC} + 0.5V for pulse durations less than 20 ns.
7. Overshoot and undershoot specifications are characterized and are not 100% tested.
8. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms



Parameters	1.8V (V_{CC})	Unit
R1	14000	Ω
R2	14000	Ω
R_{TH}	7000	Ω
V_{TH}	0.90	V

Switching Characteristics Over the Operating Range[9, 10, 11, 15, 14]

Parameter	Description	70 ns		Unit
		Min.	Max.	
Read Cycle				
t_{RC} [13]	Read Cycle Time	70	40000	ns
t_{CD}	Chip Deselect Time $\overline{CE}_1$ = HIGH or CE_2 = LOW, $\overline{BLE}/\overline{BHE}$ High Pulse Time	15		ns
t_{AA}	Address to Data Valid		70	ns
t_{OHA}	Data Hold from Address Change	5		ns
t_{ACE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Data Valid		70	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		35	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[10, 11, 12]	5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[10, 11, 12]		25	ns
t_{LZCE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Low Z[10, 11, 12]	10		ns
t_{HZCE}	$\overline{CE}_1$ HIGH and CE_2 LOW to High Z[10, 11, 12]		25	ns
t_{DBE}	$\overline{BLE}/\overline{BHE}$ LOW to Data Valid		70	ns
t_{LZBE}	$\overline{BLE}/\overline{BHE}$ LOW to Low Z[10, 11, 12]	5		ns
t_{HZBE}	$\overline{BLE}/\overline{BHE}$ HIGH to High Z[10, 11, 12]		25	ns

Notes:
9. Test conditions for all parameters other than tri-state parameters assume signal transition time of 1 ns/V, timing reference levels of $V_{CC(typ.)}/2$, input pulse levels of 0V to V_{CC}, and output loading of the specified I_{OL}/I_{OH} as shown in the "AC Test Loads and Waveforms" section.
10. At any given temperature and voltage conditions t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device. All low-Z parameters will be measured with a load capacitance of 30 pF (3V).
11. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high -impedence state.
12. High-Z and Low-Z parameters are characterized and are not 100% tested.
13. If invalid address signals shorter than min.tRC are continuously repeated for 40 μs, the device needs a normal read timing (t_{RC}) or needs to enter standby state at least once in every 40 μs.
14. In order to achieve 70-ns performance, the read access must be Chip Enable ($\overline{CE}_1$ or CE_2) controlled. That is, the addresses must be stable prior to Chip Enable going active.

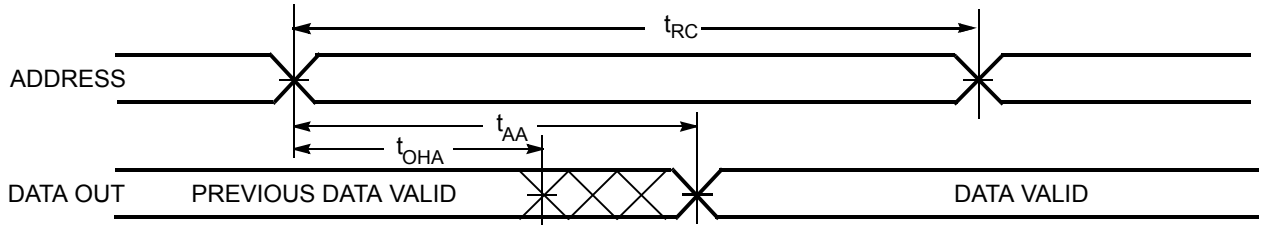
Switching Characteristics Over the Operating Range[9, 10, 11, 15, 14] (continued)

Parameter	Description	70 ns		Unit
		Min.	Max.	
Page Read Cycle				
t_{PC}	Page Mode Read Cycle Time	35	40000	ns
t_{PA}	Page Mode Address Access		35	ns
Write Cycle[15]				
t_{WC}	Write Cycle Time	70	40000	ns
t_{SCE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Write End	60		ns
t_{AW}	Address Set-Up to Write End	60		ns
t_{CD}	Chip Deselect Time $\overline{CE}_1$ = HIGH or CE_2 = LOW, $\overline{BLE}/\overline{BHE}$ High Pulse Time	15		ns
t_{HA}	Address Hold from Write End	0		ns
t_{SA}	Address Set-Up to Write Start	0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	50		ns
t_{BW}	$\overline{BLE}/\overline{BHE}$ LOW to Write End	60		ns
t_{SD}	Data Set-Up to Write End	25		ns
t_{HD}	Data Hold from Write End	0		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[10, 11, 12]		25	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[10, 11, 12]	10		ns

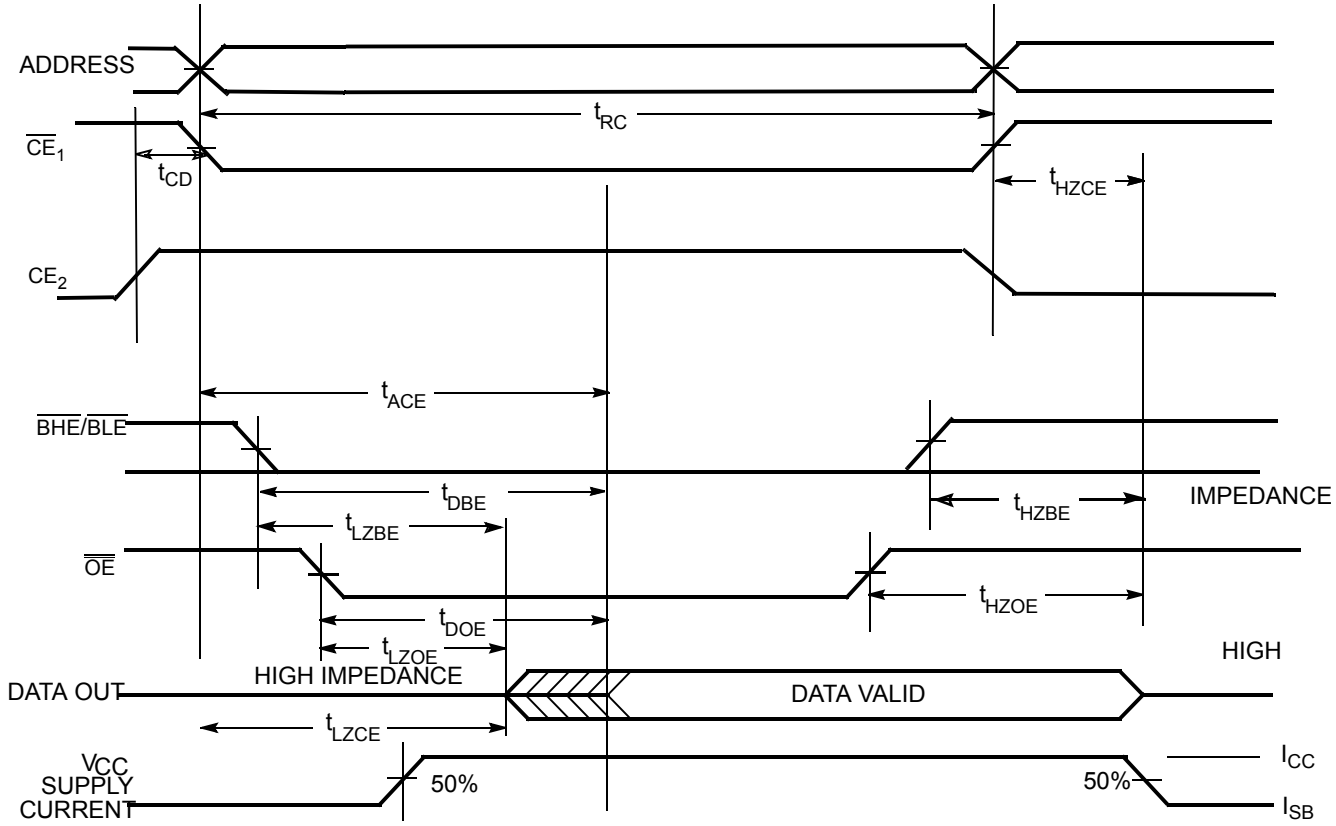
Note:
15. The internal Write time of the memory is defined by the overlap of $\overline{WE}$,$\overline{CE}_1$ = V_{IL} or CE_2 = V_{IH}, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

Switching Waveforms

Read Cycle 1 (Address Transition Controlled)[17, 18]



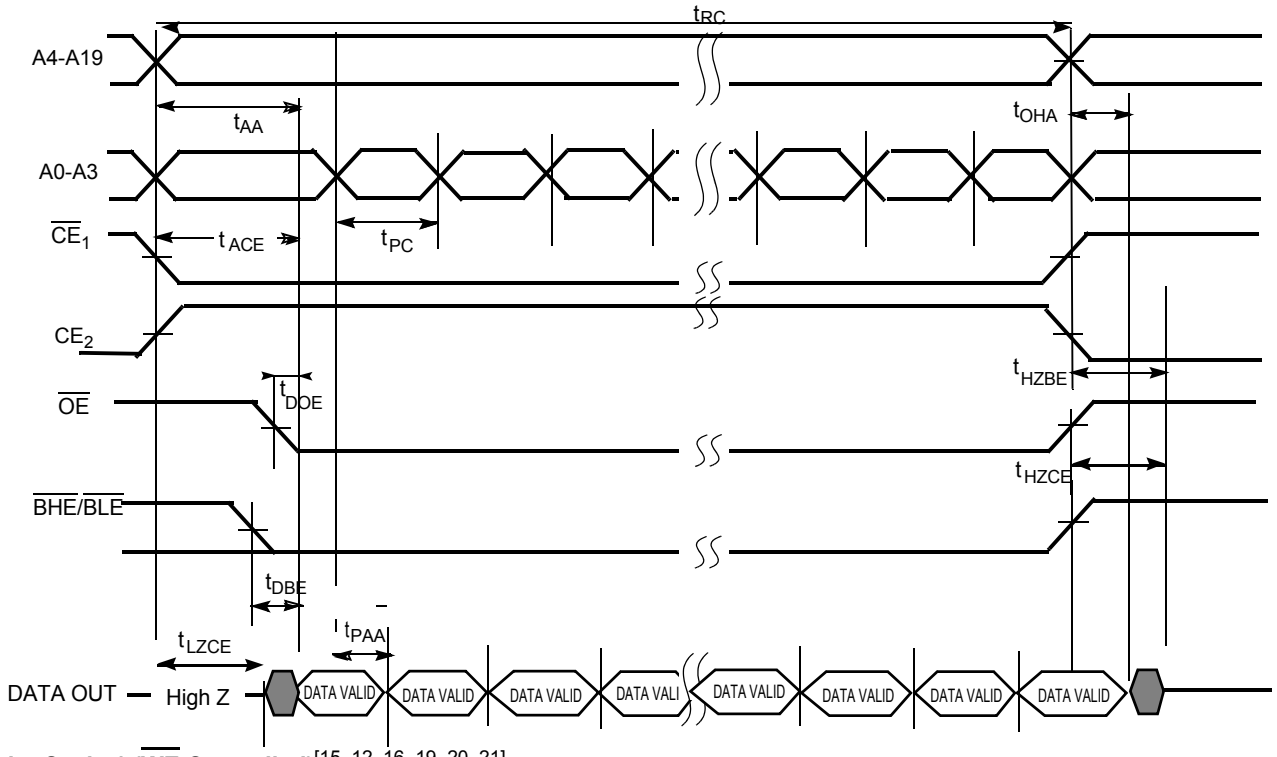
Read Cycle 2 ($\overline{OE}$ Controlled)[16, 18,19]



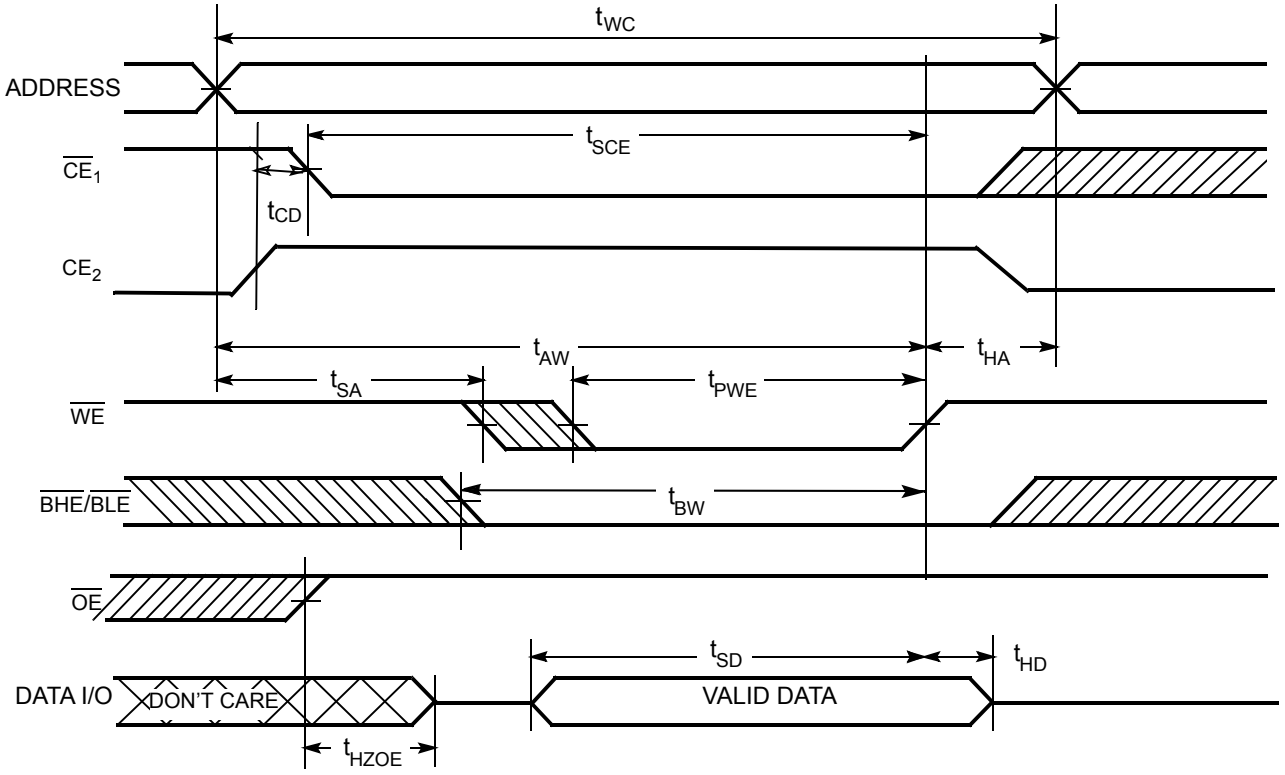
Notes:
16. Whenever $\overline{CE}_1$ = HIGH or CE_2 = LOW, $\overline{BHE}$ / $\overline{BLE}$ are taken inactive, they must remain inactive for a minimum of 5 ns.
17. Device is continuously selected. $\overline{OE}$ = $\overline{CE}_1$ = V_{IL} and CE_2 = V_{IH}.
18. $\overline{WE}$ is HIGH for Read Cycle.
19. $\overline{CE}$ is the Logical AND of $\overline{CE}_1$ and CE_2.

Switching Waveforms (continued)

Page Read Cycle ($\overline{WE}$ = V_{IH}, 16 word access)[13, 18, 19]



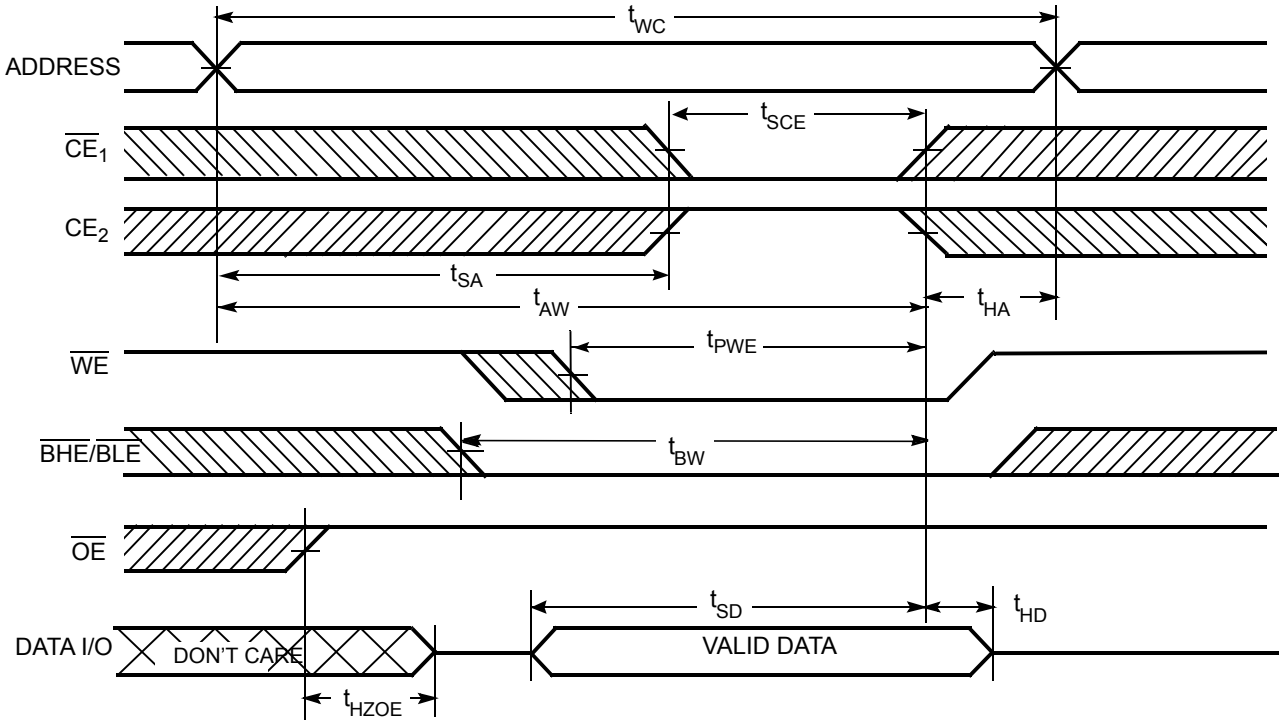
Write Cycle 1 ($\overline{WE}$ Controlled)[15, 12, 16, 19, 20, 21]



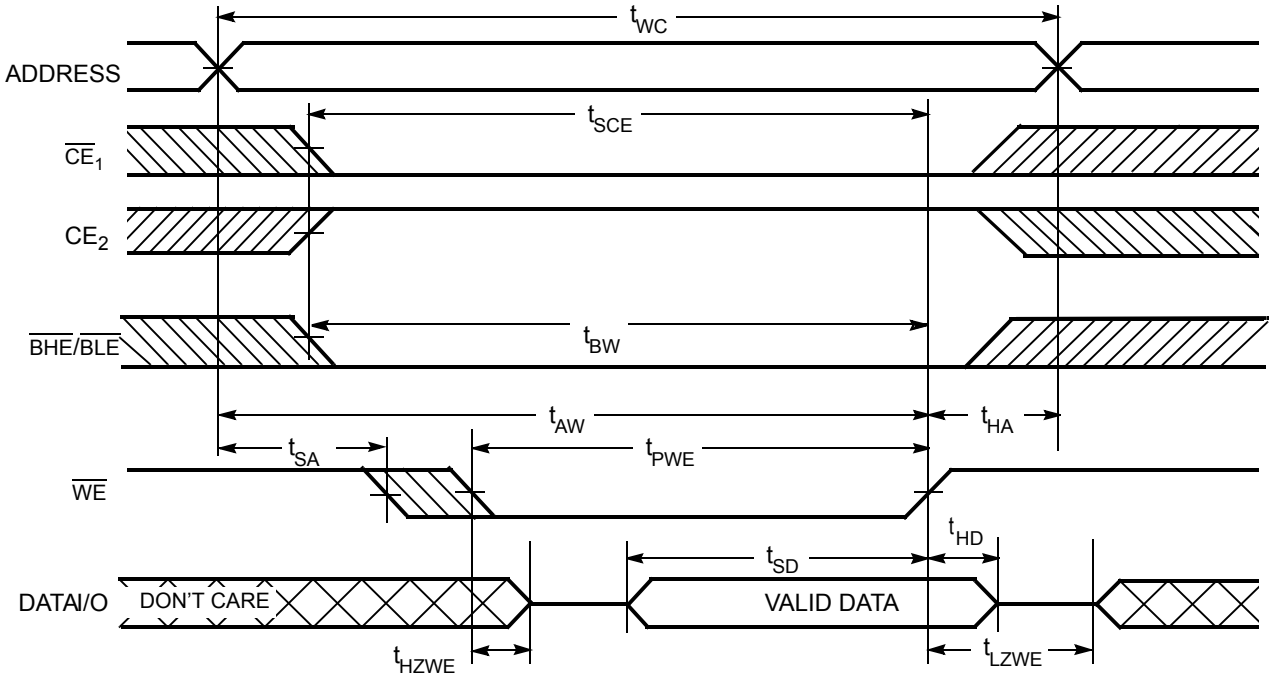
Notes:
20. Data I/O is high-impedance if $\overline{OE} \geq V_{IH}$.
21. During the DON'T CARE period in the DATA I/O waveform, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle 2 ($\overline{CE_1}$ or CE_2 Controlled)[15, 12, 16, 20, 21]

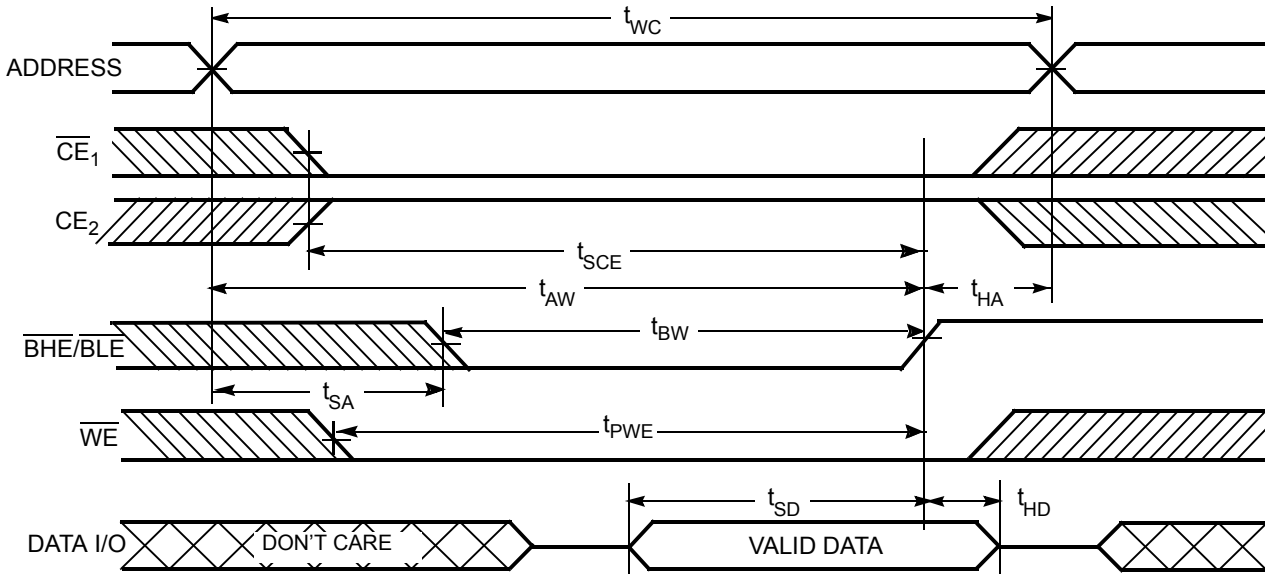


Write Cycle 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)[16, 21]



Switching Waveforms (continued)

Write Cycle 4 ($\overline{BHE}$/$\overline{BLE}$ Controlled, $\overline{OE}$ LOW)[15, 16, 20, 21]



Truth Table[22]

$\overline{CE}_1$	CE_2	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
X	L	X	X	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
X	X	X	X	H	H	High Z	Deselect/Power-down	Standby (I_{SB})
L	H	H	L	L	L	Data Out (I/O_0–I/O_{15})	Read	Active (I_{CC})
L	H	H	L	H	L	Data Out (I/O_0–I/O_7); I/O_8–I/O_{15} in High Z	Read	Active (I_{CC})
L	H	H	L	L	H	Data Out (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Read	Active (I_{CC})
L	H	H	H	L	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	H	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	H	High Z	Output Disabled	Active (I_{CC})
L	H	L	X	L	L	Data In (I/O_0–I/O_{15})	Write (Upper Byte and Lower Byte)	Active (I_{CC})
L	H	L	X	H	L	Data In (I/O_0–I/O_7); I/O_8–I/O_{15} in High Z	Write (Lower Byte Only)	Active (I_{CC})
L	H	L	X	L	H	Data In (I/O_8–I/O_{15}); I/O_0 –I/O_7 in High Z	Write (Upper Byte Only)	Active (I_{CC})

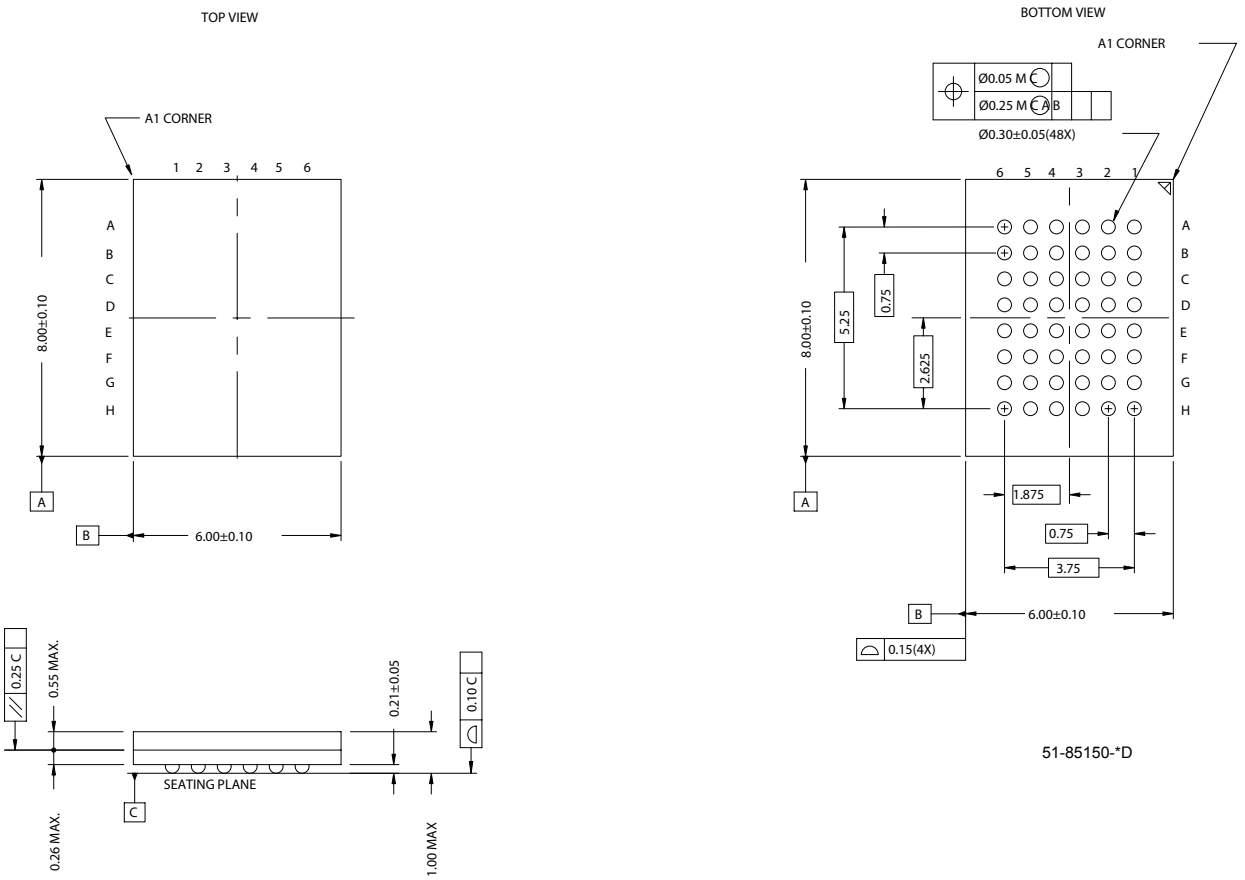
Note:
22. H = Logic HIGH, L = Logic LOW, X = Don't Care.

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
70	CYU01M16SFCU-70BVXI	BV48	48-ball Fine Pitch VBGA (6 mm × 8 mm × 1 mm) (Pb-Free)	Industrial

Package Diagram

48-ball VFBGA (6 x 8 x 1 mm) BV48



Document History Page

Document Title: CYU01M16SFCU MoBL3™ 16-Mbit (1M x 16) Pseudo Static RAM Document Number: 38-05603				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	342199	See ECN	PCI	New Datasheet
*A	386551	See ECN	PCI	Changed from Advance to Preliminary Replaced TBDs with appropriate values Changed t_{PC} and t_{PA} from 20 to 25 ns Corrected footnote # 16 as $\overline{OE}$ = $\overline{CE}_1$ = V_{IL} **and** CE_2 = V_{IH} Added separate waveforms for $\overline{CE}_1$ and CE_2 in Read #2, Page Read and Write#1 Timing diagram
*B	422623	See ECN	HRT	Removed the 55-ns Speed Bin Changed Isb2 Max value from 60 μA to 70 μA Added Isb1 to the DC parameters Added Chip Enable Access Foot Note to AC Parameters Changed the t_{CD} Min value from 5 ns to 15 ns Changed the Page Mode Values (t_{PC} and t_{PAA}) from 25 ns to 35 ns